

Guang Hui Yu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Epitaxial Growth of 6 in. Single-Crystalline Graphene on a Cu/Ni (111) Film at 750 Å°C via Chemical Vapor Deposition. <i>Small</i> , 2019, 15, e1805395.	10.0	71
2	Invisible growth of microstructural defects in graphene chemical vapor deposition on copper foil. <i>Carbon</i> , 2016, 96, 237-242.	10.3	43
3	Wrinkle-dependent hydrogen etching of chemical vapor deposition-grown graphene domains. <i>Carbon</i> , 2014, 70, 75-80.	10.3	29
4	Single-Crystal MoS ₂ Monolayer Wafer Grown on Au (111) Film Substrates. <i>Small</i> , 2021, 17, e2100743.	10.0	29
5	Mechanism of SiO _x particles formation during CVD graphene growth on Cu substrates. <i>Carbon</i> , 2018, 139, 989-998.	10.3	21
6	Stripe distributions of graphene-coated Cu foils and their effects on the reduction of graphene wrinkles. <i>RSC Advances</i> , 2015, 5, 96587-96592.	3.6	20
7	Edge morphology evolution of graphene domains during chemical vapor deposition cooling revealed through hydrogen etching. <i>Nanoscale</i> , 2016, 8, 4145-4150.	5.6	16
8	Realizing controllable graphene nucleation by regulating the competition of hydrogen and oxygen during chemical vapor deposition heating. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 23638-23642.	2.8	15
9	Facile and rigorous route to distinguish the boundary structure of monolayer MoS ₂ domains by oxygen etching. <i>Applied Surface Science</i> , 2020, 510, 145412.	6.1	15
10	Effect of Hydrogen in Size-Limited Growth of Graphene by Atmospheric Pressure Chemical Vapor Deposition. <i>Journal of Electronic Materials</i> , 2015, 44, 79-86.	2.2	14
11	Epitaxial growth of wafer scale antioxidant single-crystal graphene on twinned Pt(111). <i>Carbon</i> , 2021, 181, 225-233.	10.3	12
12	Effects of carbon-based impurities on graphene growth. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 15419-15423.	2.8	11
13	Fast and controllable synthesis of AB-stacked bilayer MoS ₂ for photoelectric detection. <i>2D Materials</i> , 2022, 9, 015016.	4.4	11
14	Role of hydrogen and oxygen in the study of substrate surface impurities and defects in the chemical vapor deposition of graphene. <i>Carbon</i> , 2021, 185, 82-95.	10.3	10
15	Conversion of the stacking orientation of bilayer graphene through high-pressure treatment. <i>Carbon</i> , 2021, 172, 480-487.	10.3	6
16	Crack-and-Fold Style Defects in CVD Graphene on Raw Cu Foils. <i>Journal of Electronic Materials</i> , 2020, 49, 4403-4409.	2.2	5
17	Single-Crystal Graphene Wafers: Epitaxial Growth of 6 in. Single-Crystalline Graphene on a Cu/Ni (111) Film at 750 Å°C via Chemical Vapor Deposition (<i>Small</i> 22/2019). <i>Small</i> , 2019, 15, 1970120.	10.0	0